

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IPD50R800CE,IIPD50R800CE

• FEATURES

- Static drain-source on-resistance: $R_{DS}(on) \leqslant 800 m_{\Omega}$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

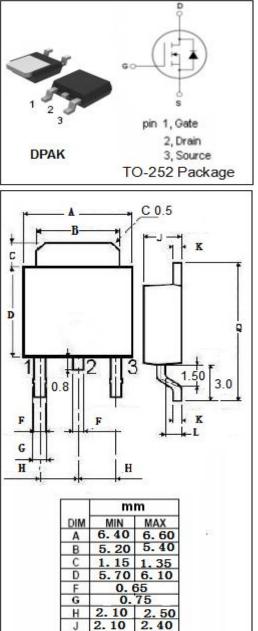
· Fast switching

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C

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SYMBOL	PARAMETER	VALUE	UNIT	¢
V _{DSS}	Drain-Source Voltage	500	V	
V_{GS}	Gate-Source Voltage	±20	V	D
lь	Drain Current-Continuous	7.6	А	Ł
I _{DM}	Drain Current-Single Pulsed	15.5	А	
P _D	Total Dissipation @T _c =25°C	60	W	-
Tj	Max. Operating Junction Temperature	150	°C	F
T _{stg}	Storage Temperature	-55~150	°C	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(j-c)	Channel-to-case thermal resistance	2.07	°C/W
Rth(j-a)	Rth(j-a) Channel-to-ambient thermal resistance		°C/W



κ

0

0.40

0.90

9.90

0.60

10

10



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =1mA	500			V
V _{GS} (th)	Gate Threshold Voltage	VDS=VGS; I _D =0.13 µ A	2.5		3.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =13V; I _D =1.3A			800	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V			0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =500V; V _{GS} = 0V			1	μA
V _{SD}	Diode forward voltage	I _F =1.9A, V _{GS} = 0V		0.83		V

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